

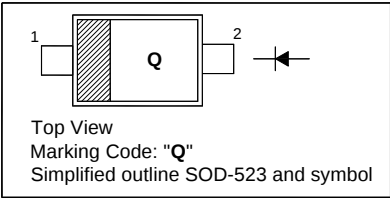
1SS413

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

for high speed switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

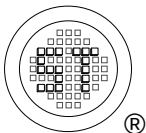


Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	25	V
Reverse Voltage	V _R	20	V
Peak Forward Current	I _{FM}	100	mA
Average Forward Current	I _O	50	mA
Surge Current (10 ms)	I _{FSM}	1	A
Power Dissipation	P _{tot}	100	mW
Junction Temperature	T _J	125	°C
Storage Temperature	T _{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

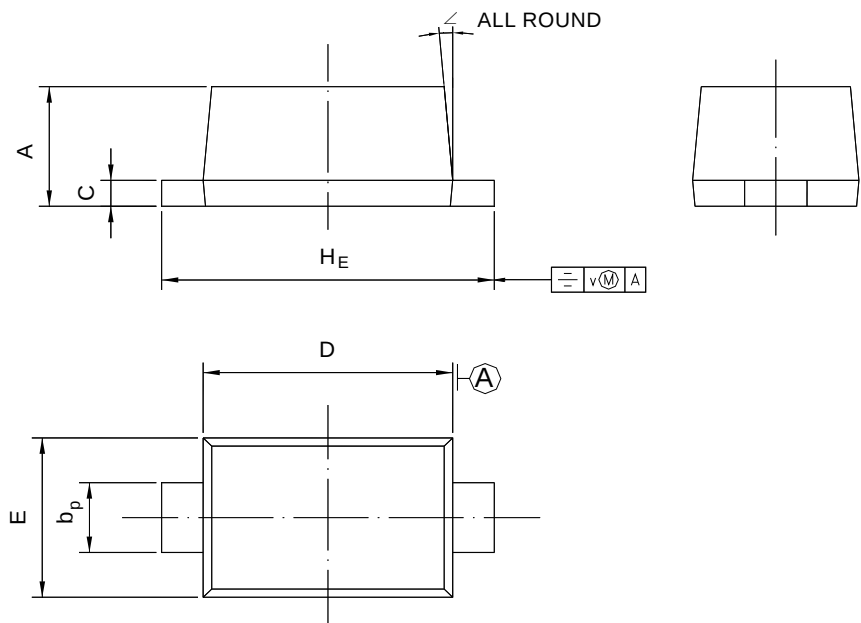
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I _F = 50 mA	V _F	-	0.55	V
Reverse Current at V _R = 20 V	I _R	-	0.5	μA
Total Capacitance at V _R = 0 V, f = 1 MHz	C _T	3.9	-	pF



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

